

Beginning at page 36, line 5,

In the present embodiment, a mesh electrode 101 for accelerating reactive species is provided between a substrate 1 and a catalyzer 46 as shown in Fig. 8, in the DC-bias catalyzed CVD method and the device therefor of the first embodiment.

Beginning at page 37, line 7,

Therefore, in the present embodiment, since the mesh electrodes 101a and 101b exist on both sides of the catalyzer 46, it is easy to direct the generated reactive species toward the substrate 1. It is desired that the mesh electrodes 101a and 101b are made or a material having high heat resistance property, and preferably having the same melting point as that of the catalyzer 46 or higher.

#### REMARKS

This is in full and timely response to the Official Action dated December 21, 2001 (Paper No. 5). One month was allotted for reply to the election of invention requirement.

The applicants, through their representatives and attorneys, hereby elect the invention of Group I, having claims 1 to 22, drawn to a method. This requirement is respectfully traversed in that the reasons advanced are not fully understood. It appears that the inventions listed in group II correspond to various species, but that the same argument is not advanced as to Group I. Accordingly, the election of Group I is not perceived as

requiring a further election of species. If a species election were required, Species I is respectfully elected, with the method claims corresponding to the apparatus claim alleged to read on the elected species, with at least claim 1 to be generic to all method claims.

A few changes are made to the specification to prepare this application for its initial examination on its merits, at least as to Group I. Entry of these changes is respectfully requested.

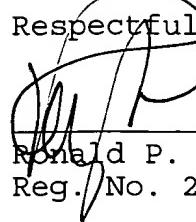
It is also noted that an Information Disclosure Statement was provided with the application as filed, citing among other documents the Japanese publication noted in the first paragraph on page 3 of the specification as filed. Consideration of those documents is respectfully requested.

The election requirement is traversed in that it is not shown that the International Application has also been so restricted for an alleged lack of unity of invention.

Nevertheless, the Applicant reserves its right to present claims to Group II in a divisional application as of right.

Early examination on the merits of the elected Group I claims 1 to 22 is requested.

Respectfully submitted,

  
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Dated: January 22, 2002

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**APPENDIX**

Beginning at page 2, line 7,

(1) Lack of uniformity and fluctuation of a plasma field, and a non-uniform electric [field] field in plasma-induced electric charges are generated. These may cause damages and short circuits to the transistor (e.g., charge-up or discharge breakdown of a gate oxide film, discharge between wirings, and the like). Particularly, such phenomenon tends to occur at the time of switching on/off the plasma.

Beginning at page 4, line 8,

[Disclosure] Summary of the Invention

Beginning at page 7, line 2,

(6) Even when the temperature of the base is lowered, the large kinetic energy of the reactive species enables formation of a film of good quality. therefore, the temperature of the base can be further lowered and a large and inexpensive insulating substrate such as a glass substrate or a heat-resistant resin substrate can be used to reduce the cost.

Beginning at page 10, line 1,

[Best Mode for Carrying Out the Invention] Detailed Description of the Preferred Embodiments

Beginning at page 25, line 18,

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The substrate 1 is heated [to] from the room temperature to 550°C, for example, 200 to 300°C, by the heater wire 51 in the susceptor 45, and the catalyster 46 is heated for activation to a temperature not higher than the melting point, particularly 800 to 2000°C, as a resistance wire in the hydrogen-based carrier gas, for example, by heating a tungsten wire to approximately 1650°C for activation. The reaction gas 40 is brought in contact with the heated catalyster 46 of tungsten or the like, and the shutter 47 is opened.

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Therefore, in the present embodiment, since the mesh electrodes 101a and 101b exist on both sides of the catalyster 46, it is easy to direct [te] the generated reactive species toward the substrate 1. It is desired that the mesh electrodes 101a and 101b are made of a material having high heat resistance property, and preferably having the same melting point as that of the catalyster 46 or higher.